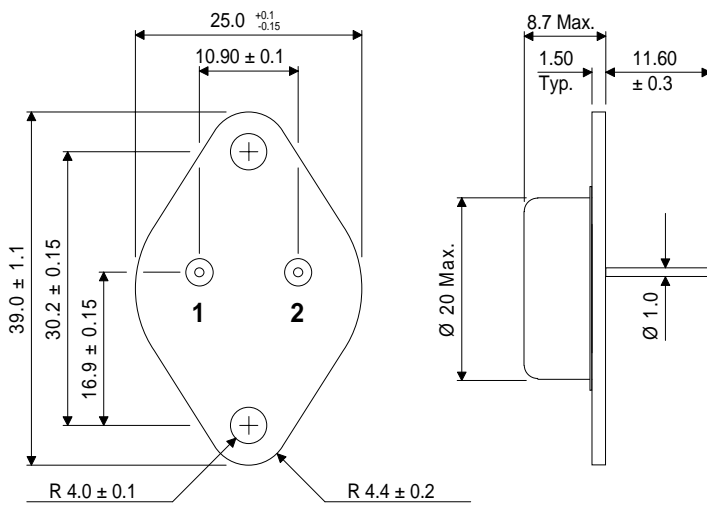


MECHANICAL DATA
Dimensions in mm

P-CHANNEL
POWER MOSFET



POWER MOSFETS FOR
AUDIO APPLICATIONS

FEATURES

- HIGH SPEED SWITCHING
- P-CHANNEL POWER MOSFET
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (160V & 200V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODE
- N-CHANNEL ALSO AVAILABLE AS BUZ900D & BUZ901D
- DOUBLE DIE PACKAGE FOR MAXIMUM POWER AND HEATSINK SPACE

TO-3

Pin 1 – Gate

Pin 2 – Drain

Case – Source

ABSOLUTE MAXIMUM RATINGS

($T_{case} = 25^{\circ}C$ unless otherwise stated)

		BUZ905D	BUZ906D
V_{DSX}	Drain – Source Voltage	-160V	-200V
V_{GSS}	Gate – Source Voltage	±14V	
I_D	Continuous Drain Current	-16A	
$I_{D(PK)}$	Body Drain Diode	-16A	
P_D	Total Power Dissipation @ $T_{case} = 25^{\circ}C$	250W	
T_{stg}	Storage Temperature Range	-55 to 150°C	
T_j	Maximum Operating Junction Temperature	150°C	
$R_{\theta JC}$	Thermal Resistance Junction – Case	0.5°C/W	

STATIC CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Characteristic		Test Conditions		Min.	Typ.	Max.	Unit
BV _{DSX}	Drain – Source Breakdown Voltage	V _{GS} = 10V	BUZ905D	-160			V
		I _D = -10mA	BUZ906D	-200			
BV _{GSS}	Gate – Source Breakdown Voltage	V _{DS} = 0	I _G = ±100µA	±14			V
V _{GS(OFF)}	Gate – Source Cut-Off Voltage	V _{DS} = -10V	I _D = -100mA	-0.1		-1.5	V
V _{DS(SAT)*}	Drain – Source Saturation Voltage	V _{GD} = 0	I _D = -16A			-12	V
I _{DSX}	Drain – Source Cut-Off Current	V _{GS} = 10V	V _{DS} = -160V BUZ905D			-10	mA
			V _{DS} = -200V BUZ906D			-10	
yfs*	Forward Transfer Admittance	V _{DS} = -10V	I _D = -3A	1.4		4	S

DYNAMIC CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Characteristic		Test Conditions		Min.	Typ.	Max.	Unit
C _{iSS}	Input Capacitance	V _{DS} = 10V f = 1MHz			1900		pF
C _{oss}	Output Capacitance				900		
C _{rSS}	Reverse Transfer Capacitance				60		
t _{on}	Turn-on Time	V _{DS} = 20V I _D = 7A			150		ns
t _{off}	Turn-off Time				110		

* Pulse Test: Pulse Width = 300µs , Duty Cycle ≤ 2%.

